

IPIC (Intelligent Power IC) High Side Solenoid Driver



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Description

The HA13705C is high side power driver IC with protectors and diagnostic function. The device is especially designed to switch inductive loads.

Functions

- Power MOS source follower output (2 A)
- With Over Voltage Shut Down circuit (OVSD)
- With Over Current protector circuit (OCSD)
- With Over Temperature Shut Down circuit (OTSD)
- With diagnostic circuit and status output
- With fail safe function under input open circuit condition
- With low voltage inhibit circuit (LVI)
- With output negative voltage clamp circuit

Features

- Protected against 60 V load dump condition
- Low R_{ON} (0.17 Ω Typ)
- Wide operating supply voltage range ($V_{DD} = 7 \text{ V to } 25 \text{ V}$)
- High sustaining voltage (-25 V)
- Protected against reverse supply voltage (-13 V)
- Protected against short circuit condition
- Input compatible with TTL, LS-TTL, or 5 V CMOS



Pin Arrangement



Block Diagram



Truth Table

Mode	In	Out	Status
Normal	L	L	L
	Н	Н	Н
Load short	L	L	L
	Н	L	L
Load open	L	Н	Н
	Н	Н	Н
Short to V _{DD}	L	Н	Н
	Н	Н	Н
OTSD ^{*1}	L	L	L
	Н	L	L
OVSD *2	L	L	Н
	Н	L	Н
LVI *3	L	L	Н
	Н	L	Н

L: Low level (0.8 V)

H: High level (2.0 V)

Notes: 1. OTSD: Over temperature shut down

2. OVSD: Over voltage shut down

3. LVI: Low voltage inhhibit

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit	Notes
Continuous supply voltage	V _{DD}	-13 to 35	V	1
Transient supply voltage	V _{DD}	60	V	2
Input voltage	V _{IN}	-0.3 to 30	V	
Output voltage	Vout	–25 to V_{DD}	V	3
Status voltage	Vs	-0.3 to +15	V	
Output current	lout	—	А	3, 4
Status current	ls	5	mA	
Power dissipation	P _T	—	W	5
Package thermal resistance/ Junction to case	өј–с	5	°C/W	
Package thermal resistance/ Junction to air	өј–а	70	°C/W	
Junction temperature range	Tj	-40 to 150	°C	
Storage temperature range	Tstg	–55 to +150	°C	

Notes: 1. Recommended operating voltage:

 $V_{DD} = 7$ to 16 V (Normal)

16 to 25 V (Jump up start 5 minutes MAX)

-13 V (Reverse Battely 5 minutes MAX)

2. Load dump condition



3. Output Transistor ASO (Reference Data)



- 4. Internally limited
- 5. Maximum power dissipation (P_{τ} (Max)) can be defined as: P_{τ} (Max) = (Tjopr(Max) – Tambient) / (θ j-c + θ c-a)
 - θ c-a: Thermal resistance between case and air (Depend on heat sink size)

ltem		Symbol	Min	Тур	Max	Unit	Test Conditions	Pin	Note
Output R	(ON)	$R_{\text{DS(ON)}}$	_	0.17	0.36	Ω	I _o = 2 A (@Tj = −40 to 150°C)	5	
Operating voltage ra	l supply inge	V_{DD}	7	—	25	V		3	
Quiescen	t current	I _{DD1}	_		0.3	mA	$V_{IN} = 0 V$, Vout = 0 V	3	
		I _{DD2}	_	6.0	10.0	mA	$V_{IN} = 5.5 V$, Vout = open	3	
Output lea	akage current	I _{LEAK}	—	—	0.1	mA	$\label{eq:V_DD} \begin{array}{l} V_{\text{DD}} = 25 \ V, \ V_{\text{IN}} = 0 \ V, \\ Vout = 0 \ V \end{array}$	5	
Input thre	shold voltage	V _{IL}	_		0.8	V		2	
		V _{IH}	2.0	_	_	V		2	
Input curr	ent	I _{IL}	-10	_	60	μA	V _{IN} = 0.8 V	2	
		I _{IH}	50	_	300	μA	V _{IN} = 5.0 V	2	
Propagati	on delay time	t _{d(ON)}	_	_	50	μs	I ₀ = 1 A	2, 5	
		t _r	_	_	90	μs	_	5	
		$t_{d(OFF)}$	_	_	50	μs	_	2, 5	
		Tf	_	_	50	μs	_	5	
Open det. current	. threshold	I _{OD}	2	10	100	μs		4, 5	
Current lin level	miter operating	I _{cs}	3.0	4.3	7.5	A		5	
LVI opera	ting level	L.V.I	_	5	6	V		3	
Over voltage shut down	Operating level	OVSD	26	29	33	V		3	
	Hysteresis	VHYS	0.15	0.5	1.5	V		3	
Output su	stain voltage	V _(SUS)	_	_	-25	V	lout = 20 mA	5	
Over temper- ature shut down	Operating level	OTSD	150	175	_	°C		5	1
	Hysteresis	THYS	_	15	_	°C		5	1
Status on	voltage	V _{SL}	_	_	0.4	V	I _s = 1 mA	4	
Status lea	akage current	I _{S(Leak)}	-10		100	μA	V _s = 5.0 V	4	

Electrical Characteristics (Ta = 25°C, V_{cc} = 12 V ±10%)

Notes: 1. Design parameter only (no test)

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Solenoid Drive Application and it's Waveform



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Package Dimensions



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